



HD74LV2G125A

Dual Bus Buffer with 3-state Output

REJ03D0099-0500Z
(Previous ADE-205-347D (Z))
Rev.5.00
Sep.30.2003

Description

The HD74LV2G125A has dual bus buffer with 3-state output in a 8 pin package. Output is disabled when the associated output enable ($\overline{\text{OE}}$) input is high. To ensure the high impedance state during power up or power down, $\overline{\text{OE}}$ should be connected to V_{CC} through a pull-down resistor; the minimum value of the resistor is determined by the current sourcing capability of the driver. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

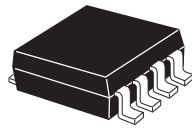
- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Electrical characteristics equivalent to the HD74LV125A
Supply voltage range : 1.65 to 5.5 V
Operating temperature range : -40 to +85°C
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
All outputs V_{O} (Max.) = 5.5 V (@ V_{CC} = 0 V, Output : Z)
- Output current ± 6 mA (@ V_{CC} = 3.0 V to 3.6 V), ± 12 mA (@ V_{CC} = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LV2G125AUSE	SSOP-8 pin	TTP-8DBV	US	E (3,000 pcs/reel)

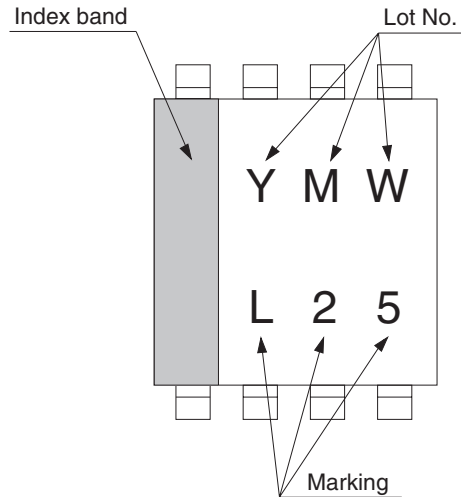
HD74LV2G125A

Outline and Article Indication

- HD74LV2G125A



SSOP-8



Y : Year code
(the last digit of year)
M : Month code
W : Week code

Function Table

Inputs		Output Y
\overline{OE}	A	
L	H	H
L	L	L
H	X	Z

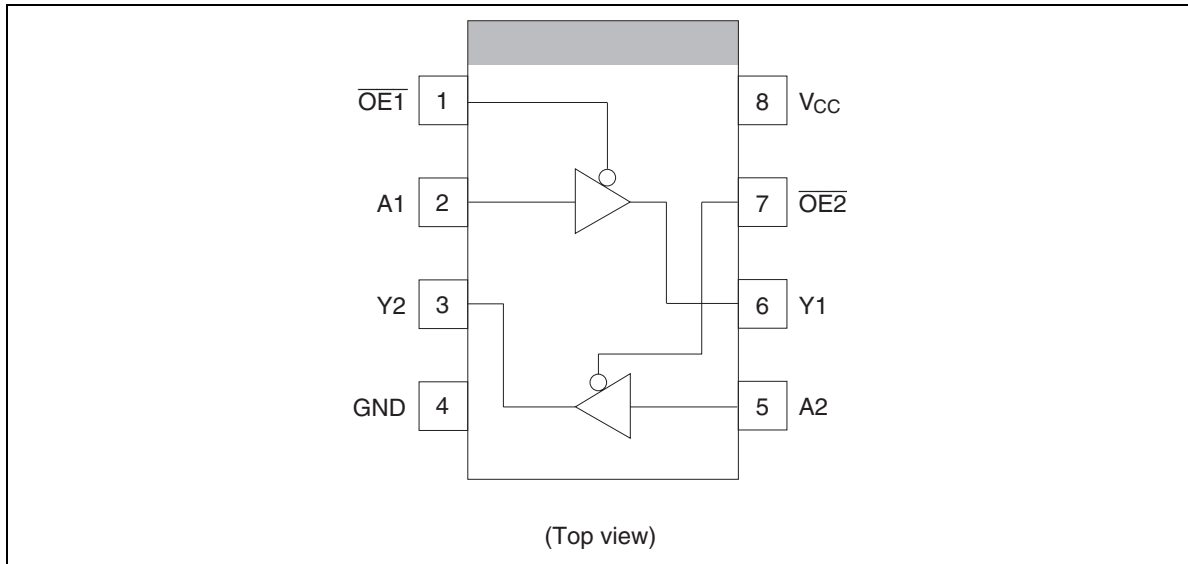
H : High level

L : Low level

X : Immaterial

Z : High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V_{CC}	-0.5 to 7.0	V	
Input voltage range ^{*1}	V_I	-0.5 to 7.0	V	
Output voltage range ^{*1, 2}	V_O	-0.5 to $V_{CC} + 0.5$ -0.5 to 7.0	V	Output : H or L V_{CC} : OFF or output : Z
Input clamp current	I_{IK}	-20	mA	$V_I < 0$
Output clamp current	I_{OK}	± 50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	± 25	mA	$V_O = 0$ to V_{CC}
Continuous current through V_{CC} or GND	I_{CC} or I_{GND}	± 50	mA	
Maximum power dissipation at $T_a = 25^\circ\text{C}$ (in still air) ^{*3}	P_T	200	mW	
Storage temperature	T_{stg}	-65 to 150	$^\circ\text{C}$	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 5.5 V maximum.
3. The maximum package power dissipation was calculated using a junction temperature of 150 $^\circ\text{C}$.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V_{CC}	1.65	5.5	V	
Input voltage range	V_I	0	5.5	V	
Output voltage range	V_O	0	V_{CC}	V	
		0	5.5		Output : Z
Output current	I_{OL}	—	1	mA	$V_{CC} = 1.65$ to 1.95 V
		—	2		$V_{CC} = 2.3$ to 2.7 V
		—	6		$V_{CC} = 3.0$ to 3.6 V
		—	12		$V_{CC} = 4.5$ to 5.5 V
	I_{OH}	—	–1		$V_{CC} = 1.65$ to 1.95 V
		—	–2		$V_{CC} = 2.3$ to 2.7 V
		—	–6		$V_{CC} = 3.0$ to 3.6 V
		—	–12		$V_{CC} = 4.5$ to 5.5 V
Input transition rise or fall rate	$\Delta t / \Delta v$	0	300	ns / V	$V_{CC} = 1.65$ to 1.95 V
		0	200		$V_{CC} = 2.3$ to 2.7 V
		0	100		$V_{CC} = 3.0$ to 3.6 V
		0	20		$V_{CC} = 4.5$ to 5.5 V
Operating free-air temperature	T_a	–40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristic

- $T_a = -40$ to 85°C

Item	Symbol	V _{CC} (V) *	Min	Typ	Max	Unit	Test condition
Input voltage	V _{IH}	1.65 to 1.95	V _{CC} ×0.75	—	—	V	
		2.3 to 2.7	V _{CC} ×0.7	—	—		
		3.0 to 3.6	V _{CC} ×0.7	—	—		
		4.5 to 5.5	V _{CC} ×0.7	—	—		
	V _{IL}	1.65 to 1.95	—	—	V _{CC} ×0.25		
		2.3 to 2.7	—	—	V _{CC} ×0.3		
		3.0 to 3.6	—	—	V _{CC} ×0.3		
		4.5 to 5.5	—	—	V _{CC} ×0.3		
Hysteresis voltage	V _H	1.8	—	0.25	—	V	V _T ⁺ – V _T [–]
		2.5	—	0.30	—		
		3.3	—	0.35	—		
		5.0	—	0.45	—		
Output voltage	V _{OH}	Min to Max	V _{CC} –0.1	—	—	V	I _{OH} = –50 μA
		1.65	1.4	—	—		I _{OH} = –1 mA
		2.3	2.0	—	—		I _{OH} = –2 mA
		3.0	2.48	—	—		I _{OH} = –6 mA
		4.5	3.8	—	—		I _{OH} = –12 mA
	V _{OL}	Min to Max	—	—	0.1	I _{OL} = 50 μA	
		1.65	—	—	0.3	I _{OL} = 1 mA	
		2.3	—	—	0.4	I _{OL} = 2 mA	
		3.0	—	—	0.44	I _{OL} = 6 mA	
		4.5	—	—	0.55	I _{OL} = 12 mA	
Input current	I _{IN}	0 to 5.5	—	—	±1	μA	V _{IN} = 5.5 V or GND
Off state output current	I _{OZ}	Min to Max	—	—	±5	μA	V _O = 5.5 V or GND
Quiescent supply current	I _{CC}	5.5	—	—	10	μA	V _{IN} = V _{CC} or GND, I _O = 0
Output leakage current	I _{OFF}	0	—	—	5	μA	V _{IN} or V _O = 0 to 5.5 V
Input capacitance	C _{IN}	3.3	—	3.0	—	pF	V _{IN} = V _{CC} or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

- $V_{CC} = 1.8 \pm 0.15 \text{ V}$

Item	Symbol	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } 85^\circ\text{C}$		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max	Min	Max				
Propagation delay time	t_{PLH}	—	13.5	23.5	1.0	26.0	ns	$C_L = 15 \text{ pF}$	A	Y
	t_{PHL}	—	19.0	33.0	1.0	36.0		$C_L = 50 \text{ pF}$		
Enable time	t_{ZH}	—	13.7	26.5	1.0	29.0	ns	$C_L = 15 \text{ pF}$	\overline{OE}	Y
	t_{ZL}	—	20.5	36.0	1.0	38.0		$C_L = 50 \text{ pF}$		
Disable time	t_{HZ}	—	8.3	20.0	1.0	22.5	ns	$C_L = 15 \text{ pF}$	\overline{OE}	Y
	t_{LZ}	—	13.0	29.5	1.0	32.0		$C_L = 50 \text{ pF}$		

- $V_{CC} = 2.5 \pm 0.2 \text{ V}$

Item	Symbol	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } 85^\circ\text{C}$		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max	Min	Max				
Propagation delay time	t_{PLH}	—	6.8	13.0	1.0	15.5	ns	$C_L = 15 \text{ pF}$	A	Y
	t_{PHL}	—	8.7	16.5	1.0	18.5		$C_L = 50 \text{ pF}$		
Enable time	t_{ZH}	—	7.0	13.0	1.0	15.5	ns	$C_L = 15 \text{ pF}$	\overline{OE}	Y
	t_{ZL}	—	8.8	16.5	1.0	18.5		$C_L = 50 \text{ pF}$		
Disable time	t_{HZ}	—	5.1	14.7	1.0	17.0	ns	$C_L = 15 \text{ pF}$	\overline{OE}	Y
	t_{LZ}	—	7.3	18.2	1.0	20.5		$C_L = 50 \text{ pF}$		

- $V_{CC} = 3.3 \pm 0.3 \text{ V}$

Item	Symbol	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } 85^\circ\text{C}$		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max	Min	Max				
Propagation delay time	t_{PLH}	—	4.8	8.0	1.0	9.5	ns	$C_L = 15 \text{ pF}$	A	Y
	t_{PHL}	—	6.1	11.5	1.0	13.0		$C_L = 50 \text{ pF}$		
Enable time	t_{ZH}	—	4.8	8.0	1.0	9.5	ns	$C_L = 15 \text{ pF}$	\overline{OE}	Y
	t_{ZL}	—	6.2	11.5	1.0	13.0		$C_L = 50 \text{ pF}$		
Disable time	t_{HZ}	—	4.1	9.7	1.0	11.5	ns	$C_L = 15 \text{ pF}$	\overline{OE}	Y
	t_{LZ}	—	5.5	13.2	1.0	15.0		$C_L = 50 \text{ pF}$		

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Switching Characteristics (cont)

- $V_{CC} = 5.0 \pm 0.5$ V

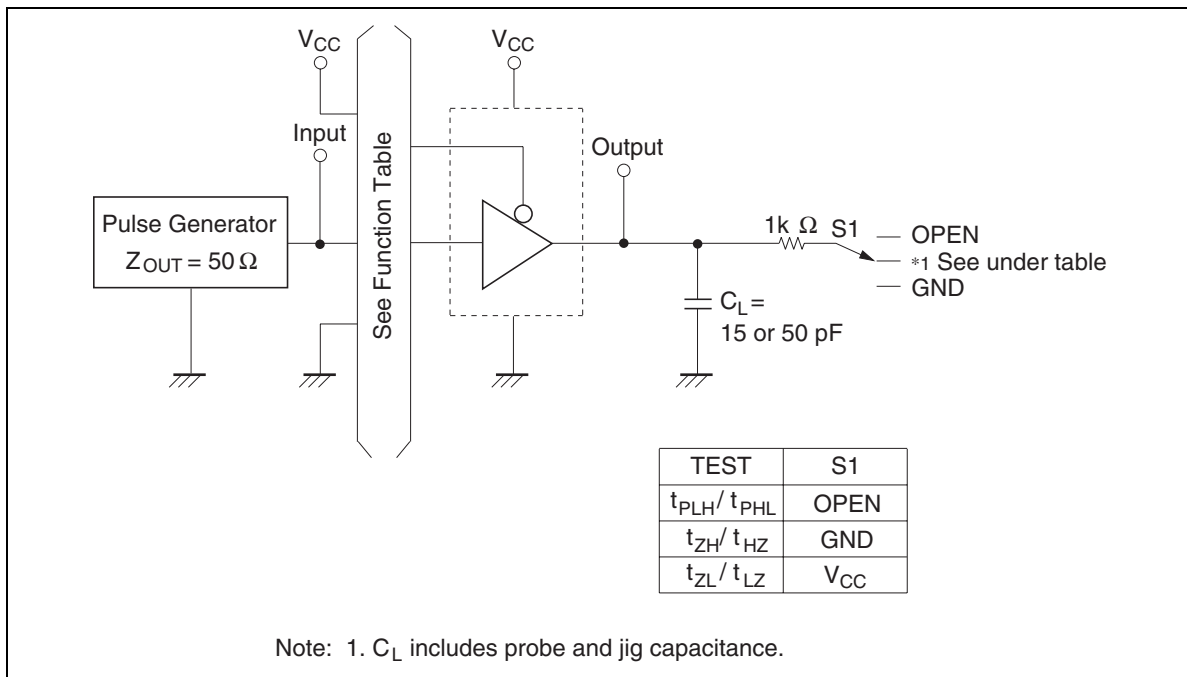
Item	Symbol	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } 85^\circ\text{C}$		Unit	Test Conditions	FROM (Input)	TO (Output)
		Min	Typ	Max	Min	Max				
Propagation delay time	t_{PLH}	—	3.4	5.5	1.0	6.5	ns	$C_L = 15$ pF	A	Y
	t_{PHL}	—	4.3	7.5	1.0	8.5		$C_L = 50$ pF		
Enable time	t_{ZH}	—	3.4	5.1	1.0	6.0	ns	$C_L = 15$ pF	\overline{OE}	Y
	t_{ZL}	—	4.4	7.1	1.0	8.0		$C_L = 50$ pF		
Disable time	t_{HZ}	—	3.2	6.8	1.0	8.0	ns	$C_L = 15$ pF	\overline{OE}	Y
	t_{LZ}	—	4.0	8.8	1.0	10.0		$C_L = 50$ pF		

Operating Characteristics

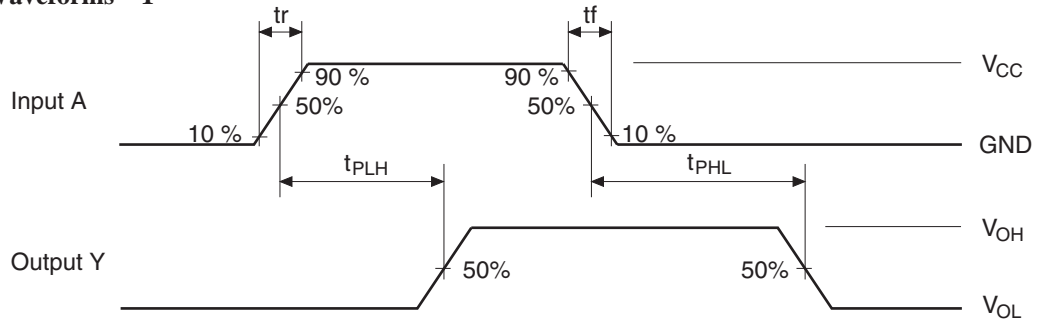
- $C_L = 50$ pF

Item	Symbol	V_{CC} (V)	$T_a = 25^\circ\text{C}$			Unit	Test Conditions
			Min	Typ	Max		
Power dissipation capacitance	C_{PD}	3.3	—	10.5	—	pF	$f = 10$ MHz
		5.0	—	11.5	—		

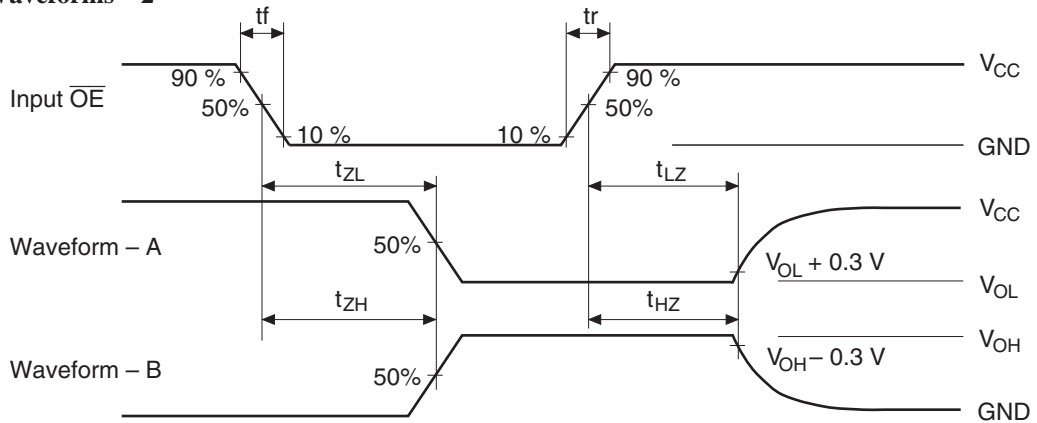
Test Circuit



• Waveforms – 1

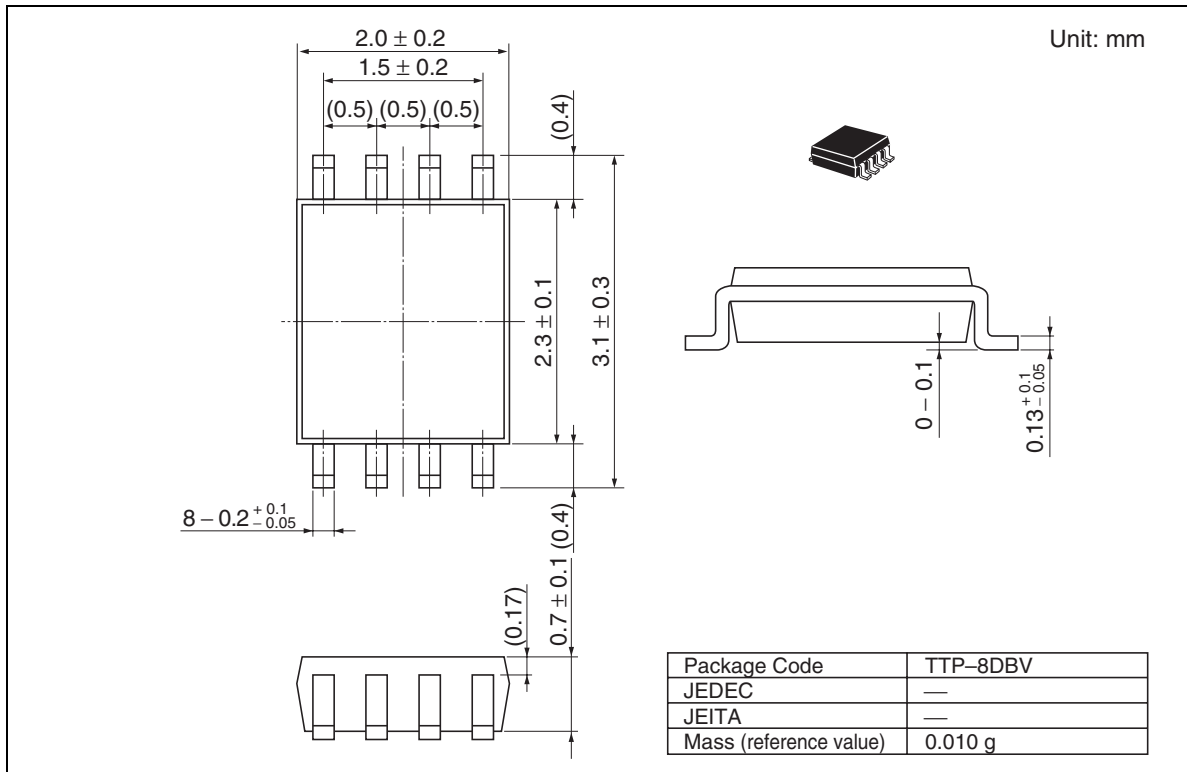


• Waveforms – 2



- Notes:
1. Input waveform : $PRR \leq 1 \text{ MHz}$, $Z_o = 50 \Omega$, $t_r \leq 3 \text{ ns}$, $t_f \leq 3 \text{ ns}$.
 2. Waveform – A is for an output with internal conditions such that the output is low except when disabled by the output control.
 3. Waveform – B is for an output with internal conditions such that the output is high except when disabled by the output control.
 4. The output are measured one at a time with one transition per measurement.

Package Dimensions



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